

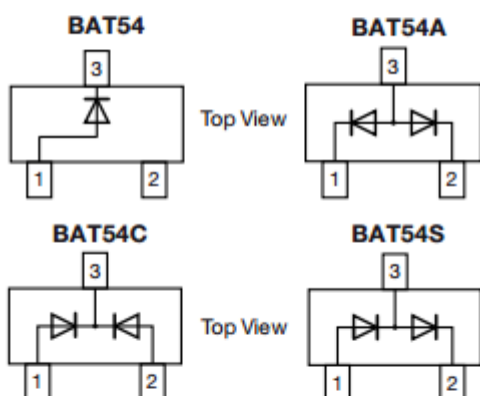


www.vishay.com

BAT54, BAT54A, BAT54C, BAT54S

Vishay Semiconductors

Small Signal Schottky Diodes, Single and Dual



FEATURES

- These diodes feature very low turn-on voltage and fast switching
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- AEC-Q101 qualified available
- Base P/N-E3 - RoHS-compliant, commercial grade
- Base P/N-HE3 - RoHS-compliant, AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT

MECHANICAL DATA

Case: SOT-23

Weight: approx. 8.8 mg

Packaging codes/options:

18/10K per 13" reel (8 mm tape), 10K/box

08/3K per 7" reel (8 mm tape), 15K/box

PARTS TABLE

PART	ORDERING CODE	INTERNAL CONSTRUCTION	TYPE MARKING	REMARKS
BAT54	BAT54-E3-08 or BAT54-E3-18	Single diode	L4	Tape and reel
	BAT54-HE3-08 or BAT54-HE3-18			
BAT54A	BAT54A-E3-08 or BAT54A-E3-18	Dual diodes common anode	L42	
	BAT54A-HE3-08 or BAT54A-HE3-18			
BAT54C	BAT54C-E3-08 or BAT54C-E3-18	Dual diodes common cathode	L43	
	BAT54C-HE3-08 or BAT54C-HE3-18			
BAT54S	BAT54S-E3-08 or BAT54S-E3-18	Dual diodes serial	L44	
	BAT54S-HE3-08 or BAT54S-HE3-18			

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Repetitive peak reverse voltage		V_{RRM}	30	V
Forward continuous current ⁽¹⁾		I_F	200	mA
Repetitive peak forward current ⁽¹⁾		I_{FRM}	300	mA
Surge forward current ⁽¹⁾	$t_p < 1\text{ s}$	I_{FSM}	600	mA
Power dissipation		P_{tot}	230	mW

Note

⁽¹⁾ Device on fiberglass substrate, see layout on next page

THERMAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance junction to ambient air	Device on fiberglass substrate, see layout on next page	R_{thJA}	430	K/W
Junction temperature		T_j	125	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-65 to +150	$^{\circ}\text{C}$
Operating temperature range		T_{op}	-55 to +125	$^{\circ}\text{C}$

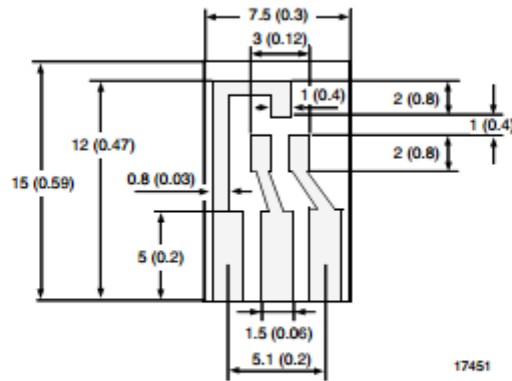
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Reverse breakdown voltage	$I_R = 100\text{ }\mu\text{A}$ (pulsed)	$V_{(BR)}$	30			V
Leakage current	Pulsed test $t_p < 300\text{ }\mu\text{s}$, $\delta < 2\%$ at $V_R = 25\text{ V}$	I_R			2	μA
Forward voltage	$I_F = 0.1\text{ mA}$, $t_p < 300\text{ }\mu\text{s}$, $\delta < 2\%$	V_F			240	mV
	$I_F = 1\text{ mA}$, $t_p < 300\text{ }\mu\text{s}$, $\delta < 2\%$	V_F			320	mV
	$I_F = 10\text{ mA}$, $t_p < 300\text{ }\mu\text{s}$, $\delta < 2\%$	V_F			400	mV
	$I_F = 30\text{ mA}$, $t_p < 300\text{ }\mu\text{s}$, $\delta < 2\%$	V_F			500	mV
	$I_F = 100\text{ mA}$, $t_p < 300\text{ }\mu\text{s}$, $\delta < 2\%$	V_F			800	mV
Diode capacitance	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_D			10	pF
Reverse recovery time	$I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$, $I_R = 1\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}			5	ns

LAYOUT FOR R_{thJA} TEST

Thickness:

Fiberglass 15 mm (0.059")

Copper leads 0.3 mm (0.012")



TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

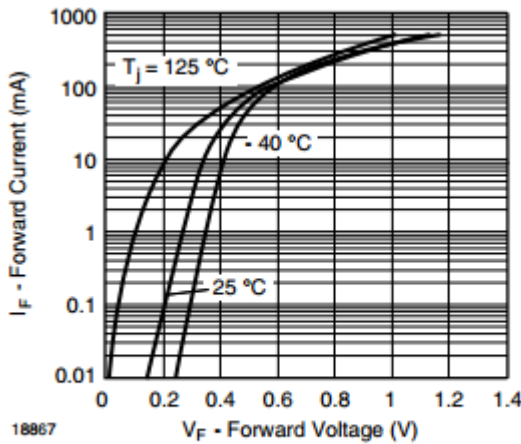


Fig. 1 - Typical Forward Voltage Forward Current vs. Various Temperatures

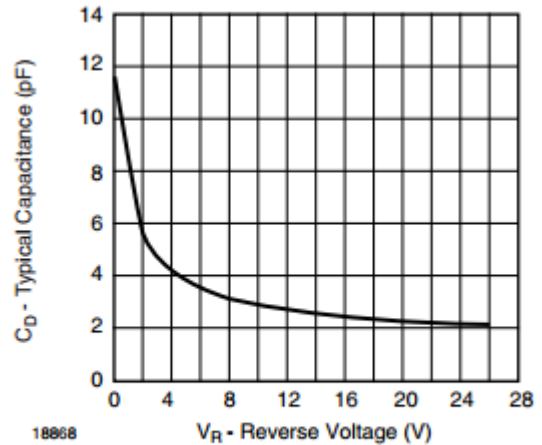


Fig. 2 - Diode Capacitance vs. Reverse Voltage V_R

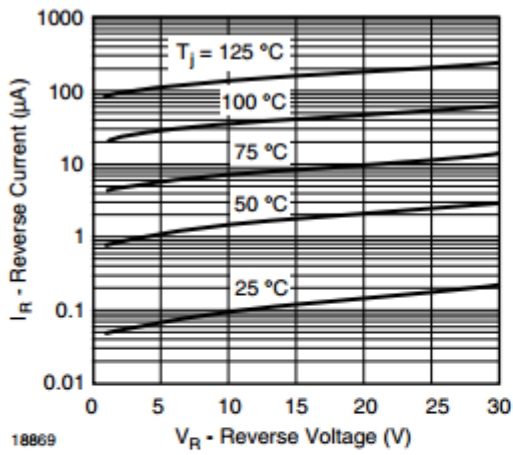
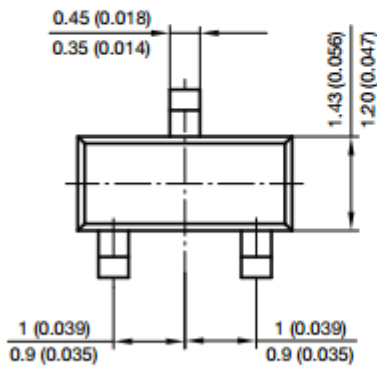
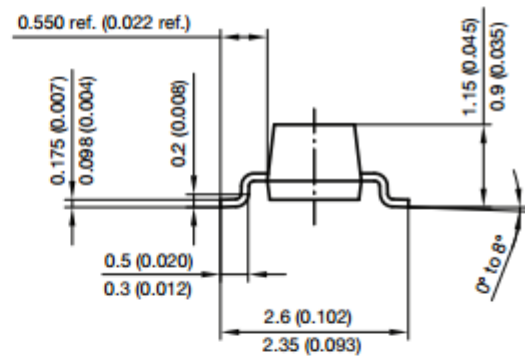
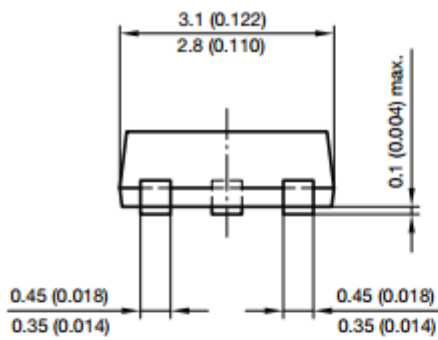


Fig. 3 - Typical Variation of Reverse Current vs. Various Temperatures

PACKAGE DIMENSIONS in millimeters (inches): **SOT-23**



Foot print recommendation:

